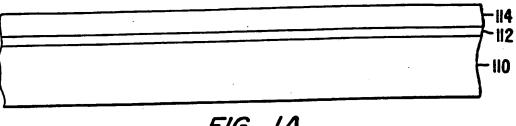
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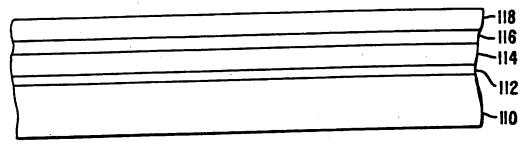


FIG. IB.

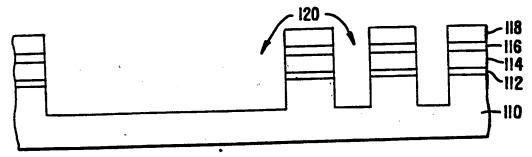


FIG. IC.

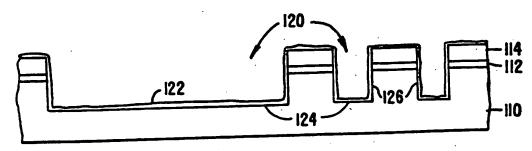
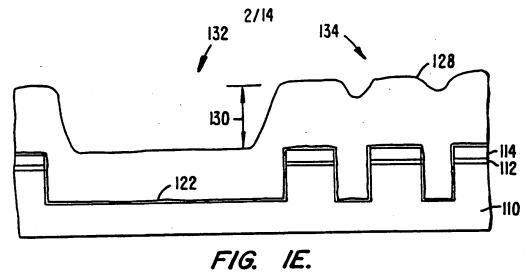
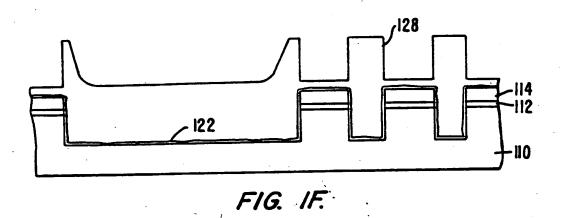
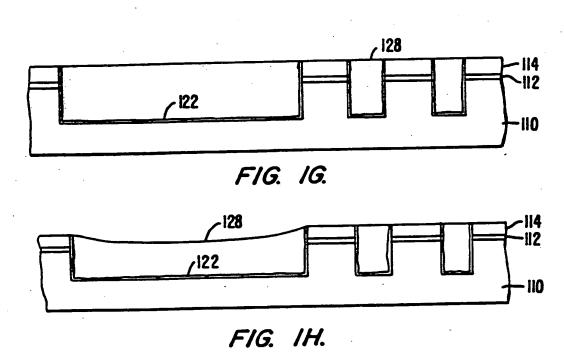


FIG. ID.

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3/14 210 APPLY CVD ARC OVER SUBSTRATE - 212 FORM PHOTO RESIST OVER CVD ARC -214 **EXPOSE PHOTORESIST** TO DEFINE TRENCH LOCATION -216 REMOVE PHOTORESIST AT TRENCH LOCATION -218 ETCH CVD ARC AND SUBSTRATE TO FORM TRENCH AT TRENCH LOCATION -220 REMOVE PHOTORESIST - 222 CLEAN TRENCH

FIG. 2A.

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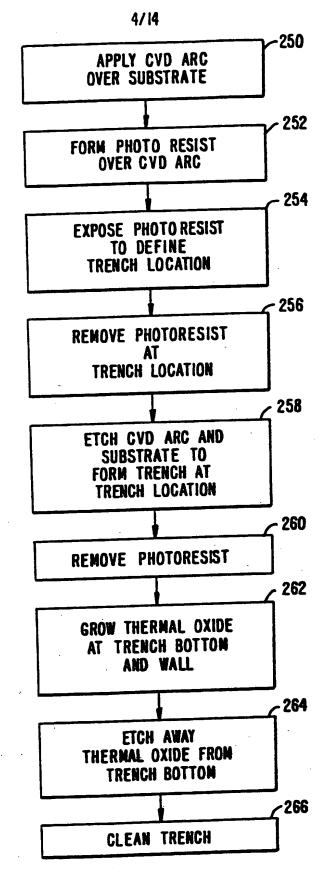
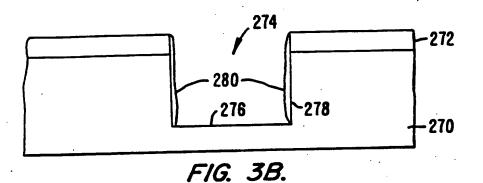


FIG. 2B.

SUBSTITUTE SHEET (RULE 26)

FIG. 3A.



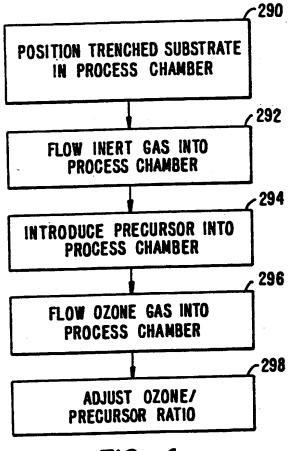


FIG. 4.

SUBSTITUTE SHEET (RULE 26)

TOPICAL PROPERTY

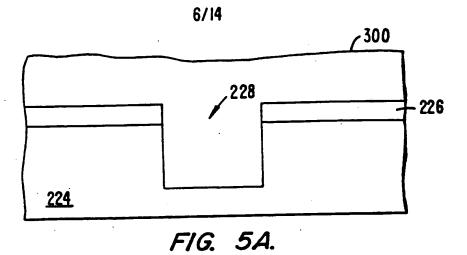
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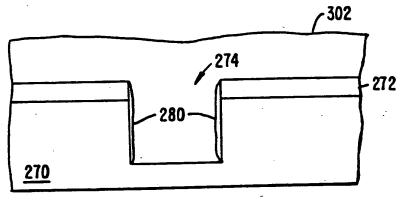


FIG. 5B.

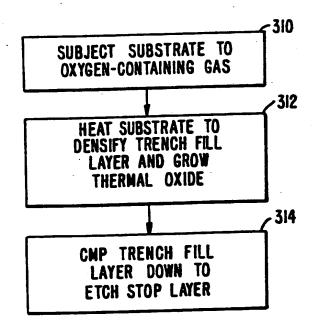


FIG. 6.

SUBSTITUTE SHEET (RULE 26)

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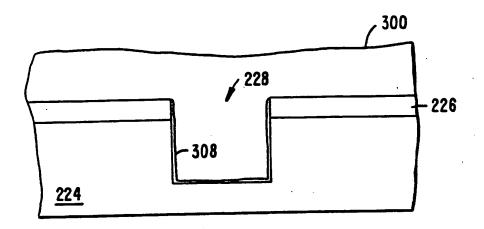
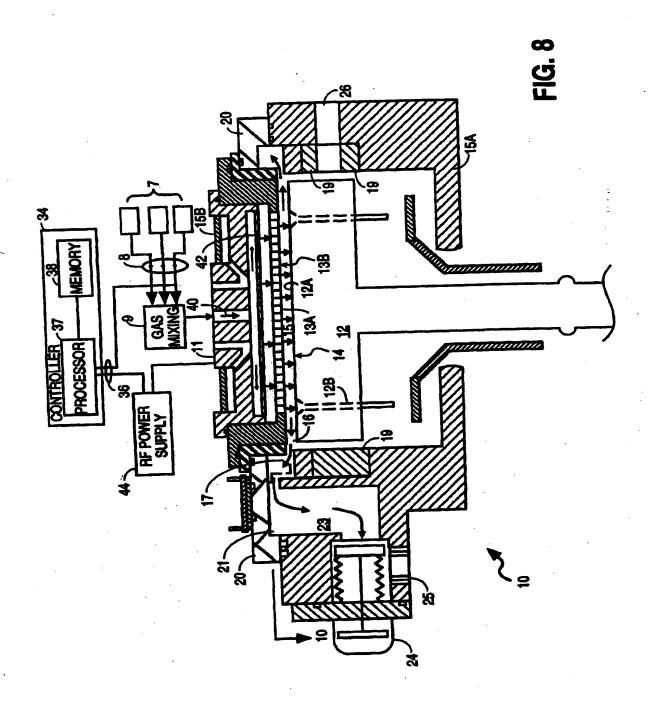


FIG. 7.

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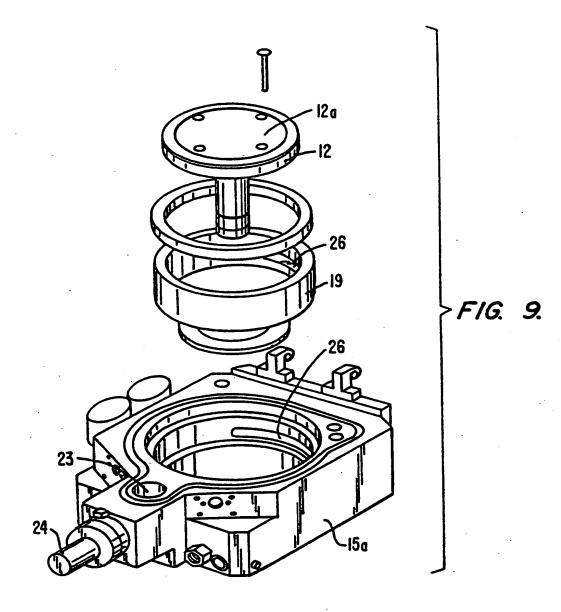


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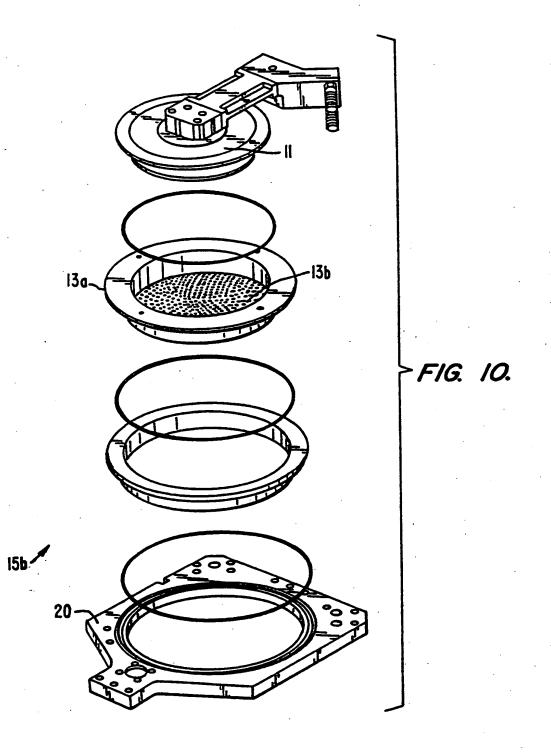
WO 99/62108

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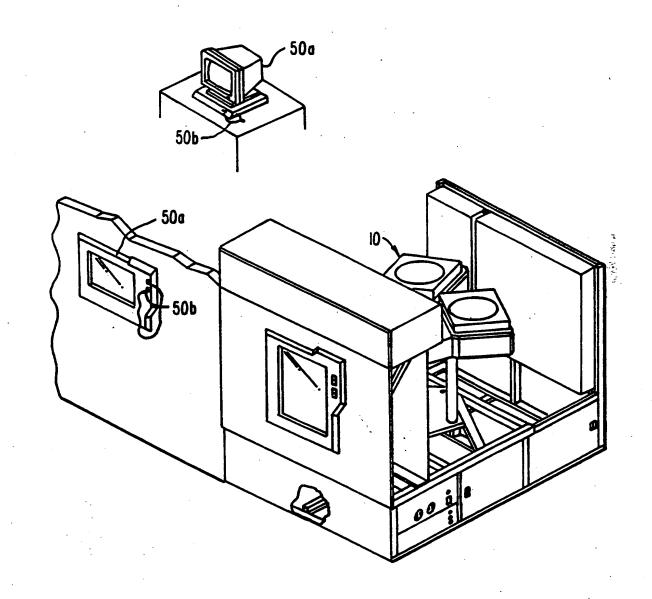


FIG. 11.

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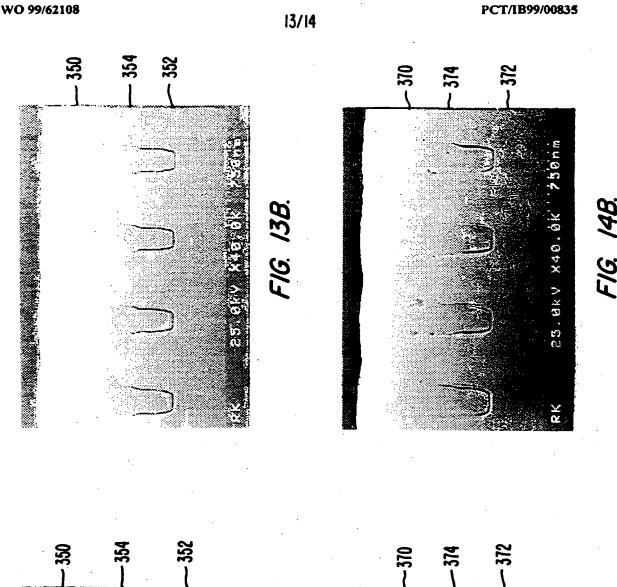
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12/14 PLASMA CONTROL CHAMBER MANAGER HEATER CONTROL CHAMBER MANAGER FOR CVD/SPUTTERING CHAMBER PRESSURE CONTROL PROCESS Sequencer PROCESS GAS CONTROL CHAMBER SELECTION PROCESS GAS FLOW TEMPERATURE PRESSURE PLASMA POWER CHAMBER MANAGER PROCESS SELECTOR SUBSTRATE Positioning



SUBSTITUTE SHEET (RULE 26)

380

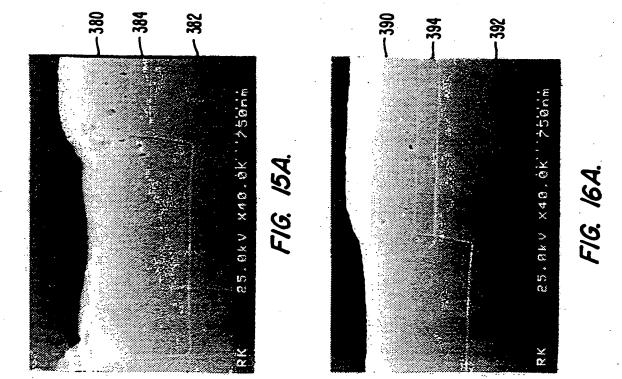
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25. OKV X4B. OK 750mm 25. OKV X4B. OK 750mm 71/6 / 68.



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